Supplementary Information for the manuscript: High quality sub-10 nm graphene nanoribbons by on-chip PS-b-PDMS block copolymer lithography, by Rasappa et al.

1. SEM image shows the confinement of graphene nanoribbons inside the SU-8 trenches.
2. Raman Intensity map showing the spatial homogeneity of graphene nanoribbons after etching.

![SEM image showing confinement of graphene nanoribbons inside SU-8 trenches.](image1.png)

**Figure SI.1**: Confinement of graphene nanoribbons inside SU-8 trenches.

![Raman maps of I(G) and I(D) of graphene nanoribbons showing spatial homogeneity.](image2.png)

**Figure SI.2**: Raman maps of I(G) and I(D) of graphene nanoribbons showing the spatial homogeneity of the ribbon width during the etching process of graphene. The ratio of both values is ~ 1 in all the positions, indicating the homogeneity achieved in the process. The spatial separation between the taken spectra is 0.5 μm in both directions.